

SEMICONDUCTOR DEVICE WITH SILICIDED SOURCE/DRAINS

Abstract of the Disclosure

5 In a semiconductor device, a relatively deep germanium implant and
activation thereof precedes deposition of the nickel for nickel silicide formation.
The activation of the germanium causes the lattice constant in the region of the
implant to be increased over the lattice constant of the background substrate,
which is preferably silicon. The effect is that the lattice so altered avoids
10 formation of nickel disilicide. The result is that the nickel silicide spiking is
avoided.